

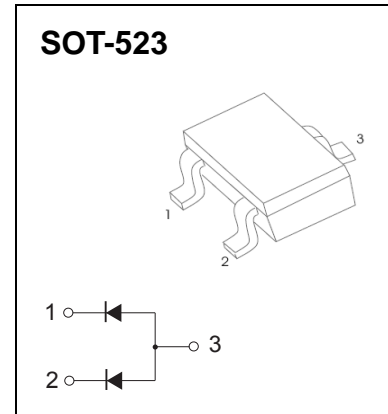
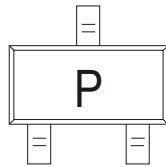
Plastic-Encapsulate Transistors

DAP222T SWITCHING DIODE

FEATURES:

- High speed
- Suitable for high packing density layout
- High reliability

MARKING: P



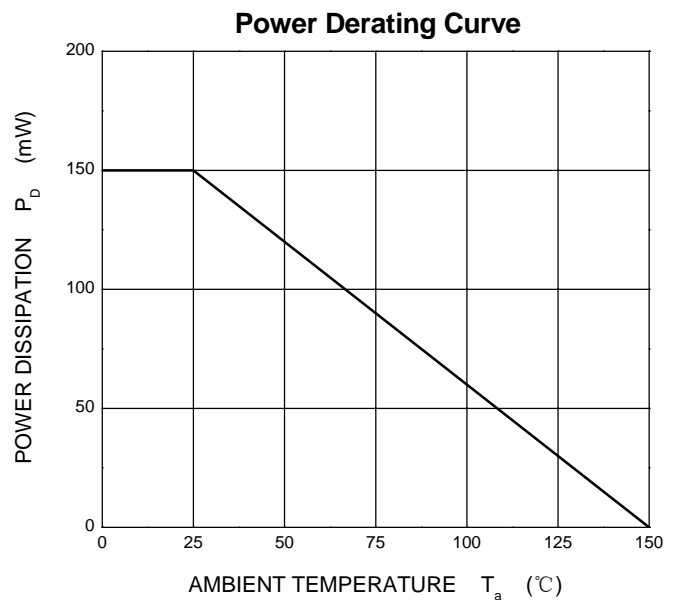
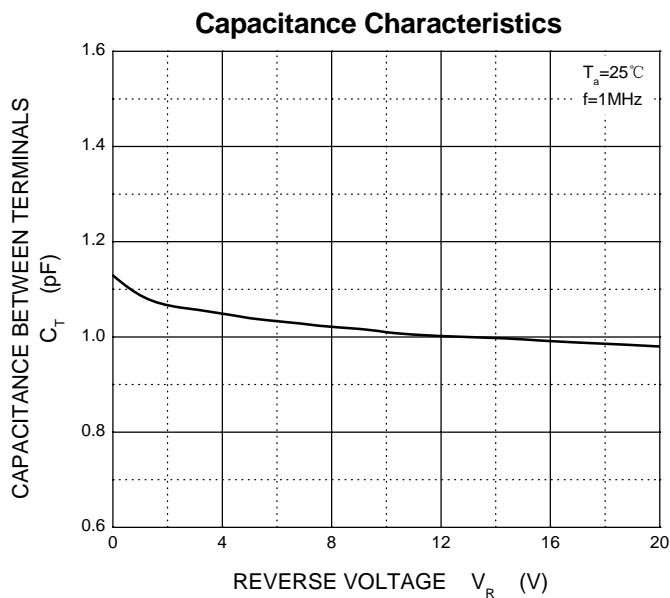
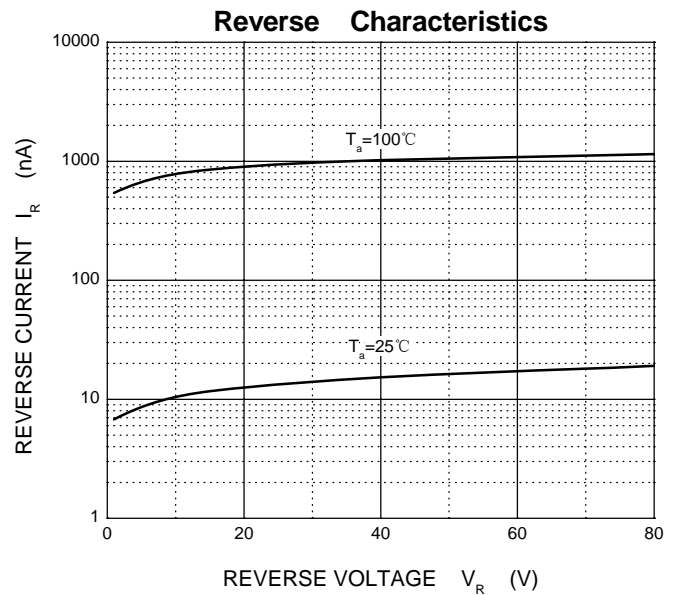
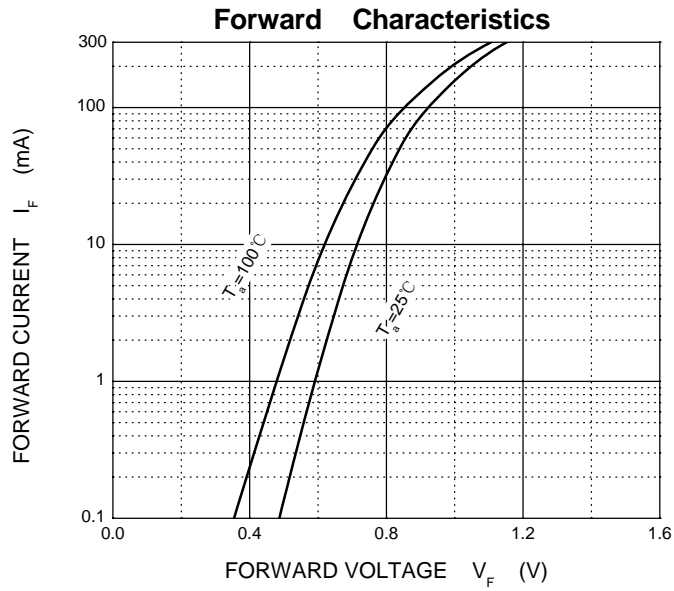
Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	80	V
DC Blocking Voltage	V_R	80	V
Forward Continuous Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	150	mW
Thermal resistance From Junction to ambient	$R_{\theta JA}$	833	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R = 70V$		0.1	μA
Forward voltage	V_F	$I_F = 100mA$		1.2	V
Diode capacitance	C_D	$V_R = 0, f = 1MHz$		3.5	pF
Reverse recovery time	t_{rr}	$V_R = 6V, I_F = I_R = 5mA$		4	ns

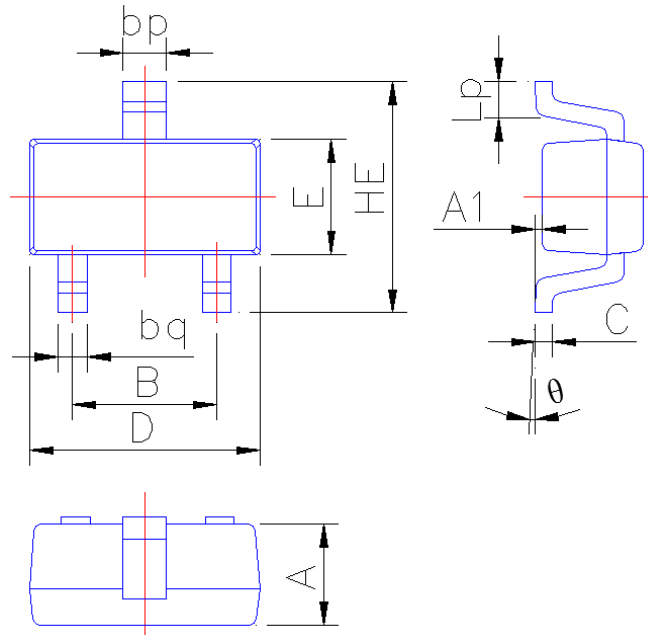
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.80
A1	0.010	0.100
B	0.95	1.05
bp	0.26	0.40
bq	0.16	0.30
C	0.09	0.15
D	1.50	1.70
E	0.70	0.85
HE	1.45	1.75
Lp	0.16	0.36
θ	0°	5°